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BOURNS

BDX34, BDX34A, BDX34B, BDX34C, BDX34D PNP SILICON POWER DARLINGTONS

- Designed for Complementary Use with BDX33, BDX33A, BDX33B, BDX33C and BDX33D
- 70 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A



This series is currently available, but not recommended for new designs.

Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDX34		-45		
Collector-base voltage (I _E = 0)	BDX34A		-60		
	BDX34B	V _{CBO}	-80	V	
	BDX34C		-100	I	
	BDX34D		-120		
	BDX34		-45		
Collector-emitter voltage ($I_B = 0$)	BDX34A		-60		
	BDX34B	V _{CEO}	-80	V	
	BDX34C		-100	l	
	BDX34D		-120		
Emitter-base voltage	V _{EBO}	-5	V		
Continuous collector current	Ι _C	-10	A		
Continuous base current	I _B	-0.3	A		
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)	P _{tot}	70	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note	P _{tot}	2	W		
Operating free air temperature range	Т _Ј	-65 to +150	°C		
Storage temperature range	T _{stg}	-65 to +150	°C		
Operating free-air temperature range	T _A	-65 to +150	°C		

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

BDX34, BDX34A, BDX34B, BDX34C, BDX34D PNP SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS				MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage					-45			
					BDX34A	-60			
		I _C = -100 mA	$I_B = 0$	(see Note 3)	BDX34B	-80			V
		0	D		BDX34C	-100			
					BDX34D	-120			
		V _{CE} = -30 V	I _B = 0		BDX34			-0.5	
		$V_{CE} = -30 V$	$I_B = 0$		BDX34A			-0.5	
		$V_{CE} = -40 V$	$I_B = 0$		BDX34B			-0.5	
		$V_{CE} = -50 V$	$I_B = 0$		BDX34C			-0.5	mA
	Collector-emitter	$V_{CE} = -60 V$	$I_B = 0$		BDX34D			-0.5	
CEO	cut-off current	$V_{CE} = -30 V$	$I_B = 0$	$T_{C} = 100^{\circ}C$	BDX34			-10	
		$V_{CE} = -30 V$	$I_B = 0$	$T_{C} = 100^{\circ}C$	BDX34A			-10	
		$V_{CE} = -40 V$	$I_B = 0$	$T_{C} = 100^{\circ}C$	BDX34B			-10	
		$V_{CE} = -50 V$	$I_B = 0$	$T_{C} = 100^{\circ}C$	BDX34C			-10	
		$V_{CE} = -60 V$	$I_B = 0$	$T_{C} = 100^{\circ}C$	BDX34D			-10	
		V _{CB} = -45 V	I _E = 0		BDX34			-1	
		V _{CB} = -60 V	$I_E = 0$		BDX34A			-1	
		V _{CB} = -80 V	$I_E = 0$		BDX34B			-1	
		V _{CB} = -100 V	$I_E = 0$		BDX34C			-1	
	Collector cut-off	V _{CB} = -120 V	$I_E = 0$		BDX34D			-1	
СВО	current	V _{CB} = -45 V	$I_E = 0$	$T_{C} = 100^{\circ}C$	BDX34			-5	mA
		V _{CB} = -60 V	$I_E = 0$	$T_{C} = 100^{\circ}C$	BDX34A			-5	
		V _{CB} = -80 V	$I_E = 0$	$T_{C} = 100^{\circ}C$	BDX34B			-5	
		V _{CB} = -100 V	$I_E = 0$	$T_{C} = 100^{\circ}C$	BDX34C			-5	
		V _{CB} = -120 V	$I_E = 0$	$T_{\rm C} = 100^{\circ}{\rm C}$	BDX34D			-5	
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	$I_{\rm C} = 0$					-10	mA
	Forward current transfer ratio	V _{CE} = -3 V	I _C = -4 A		BDX34	750			
		V _{CE} = -3 V	I _C = -4 A		BDX34A	750			
h _{FF}		V _{CE} = -3 V	I _C = -3 A	(see Notes 3 and 4)	BDX34B	750			
		V _{CE} = -3 V	I _C = -3 A		BDX34C	750			
		$V_{CE} = -3 V$	I _C = -3 A		BDX34D	750			
V _{BE(on)}	Base-emitter voltage	V _{CE} = -3 V	I _C = -4 A		BDX34			-2.5	
		$V_{CE} = -3 V$	$I_{\rm C} = -4$ A	(see Notes 3 and 4)	BDX34A			-2.5	
		$V_{CE} = -3 V$	I _C = -3 A		BDX34B			-2.5	V
		$V_{CE} = -3 V$	I _C = -3 A		BDX34C			-2.5	
		V _{CE} = -3 V	I _C = -3 A		BDX34D			-2.5	
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = -8 mA	I _C = -4 A		BDX34			-2.5	
		I _B = -8 mA	$I_{C} = -4 A$		BDX34A			-2.5	
		I _B = -6 mA	I _C = -3 A	(see Notes 3 and 4)	BDX34B			-2.5	V
		I _B = -6 mA	I _C = -3 A		BDX34C	C		-2.5	
		I _B = -6 mA	I _C = -3 A		BDX34D			-2.5	
V _{EC}	Parallel diode forward voltage	I _E = -8 A	I _B = 0					-4	V

NOTES: 3. These parameters must be measured using pulse techniques, t_p = 300 $\mu s,$ duty cycle $\leq 2\%.$

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

BDX34, BDX34A, BDX34B, BDX34C, BDX34D PNP SILICON POWER DARLINGTONS

BOURNS®

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R _{θJC}	Junction to case thermal resistance			1.78	°C/W
R _{θJA}	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{on}	Turn-on time	I _C = -3 A	I _{B(on)} = -12 mA	$I_{B(off)} = 12 \text{ mA}$		1		μs
t _{off}	Turn-off time	$V_{BE(off)} = 3.5 V$	$R_L = 10 \ \Omega$	t_p = 20 μ s, dc \leq 2%		5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TYPICAL CHARACTERISTICS

BASE-EMITTER SATURATION VOLTAGE vs **COLLECTOR CURRENT** TCS135AJ -3.0 -40°C T_c = $V_{BE(sat)}$ - Base-Emitter Saturation Voltage - V 25°C T_c = 100°C -2.5 -2.0 -1.5 -1.0 \mathbf{I}_{B} $= I_c / 100$ = 300 µs, duty cycle < 2% -0.5 -0.5 -1.0 -10 I_c - Collector Current - A



THERMAL INFORMATION



Figure 4.